

SILICON NPN RF TRANSISTOR

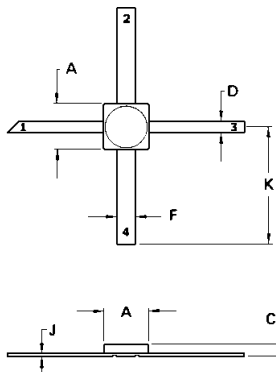
DESCRIPTION:

The **MRF572** is Designed for Low Noise General Purpose VHF,UHF Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	60 mA
V_{CE}	12 V
P_{DISS}	500 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$

PACKAGE STYLE 100MIL CERAMIC STRIPLINE



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.29	2.67	0.090	0.105
C	0.89	1.40	0.035	0.055
D	0.41	0.61	0.016	0.024
F	0.89	1.09	0.035	0.043
J	0.08	0.15	0.003	0.006
K	4.45	5.84	0.175	0.230

1 = Collector 2 & 4 = Emitter
3 = Base

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0$ mA			12			V
BV_{CBO}	$I_C = 100$ μA			20			V
I_{CBO}	$V_{CB} = 8.0$ V					200	μA
BV_{EBO}	$I_E = 50$ μA			1.5			V
h_{FE}	$V_{CE} = 8.0$ V	$I_C = 10$ mA		30		300	---
C_{cb}	$V_{CB} = 8.0$ V	$f = 1.0$ MHz			0.25		pF
f_t	$V_{CE} = 8.0$ V	$I_C = 25$ mA	$f = 1.0$ GHz		8.0		GHz
$ S_{21E} ^2$	$V_{CE} = 8.0$ V	$I_C = 25$ mA	$f = 1.0$ GHz $f = 2.0$ GHz		16.9 12.0		dB
GNF	$V_{CE} = 8.0$ V	$I_C = 0$ mA	$f = 0.5$ GHz $f = 1.0$ GHz $f = 2.0$ GHz	10	16.5 12		dB
NF	$V_{CE} = 8.0$ V	$I_C = 0$ mA	$f = 0.5$ GHz $f = 1.0$ GHz $f = 2.0$ GHz		1.0 1.5 2.5	2.0	dB